

Product Summary

$V_{(BR)DSS}$	$R_{DS(on) \max}$	I_D $T_A = +25^\circ\text{C}$
100V	220m Ω @ $V_{GS} = 10\text{V}$	1.6A
	250m Ω @ $V_{GS} = 4.5\text{V}$	1.3A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

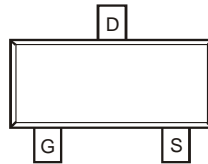
- Load Switch

Mechanical Data

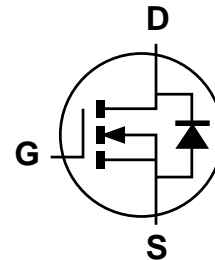
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed Over Copper Leadframe. Solderable per MIL-STD-202, Method 208 **e3**
- Weight: 0.0072 grams (Approximate)



Top View



Pin Configuration



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMN10H220L-7	Standard	SOT23	3000/Tape & Reel
DMN10H220L-13	Standard	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



N1H = Marking Code
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 ȲM = Date Code Marking for CAT (Chengdu Assembly/ Test site)
 Y or Ȳ = Year (ex: A = 2013)
 M = Month (ex: 9 = September)

Date Code Key

Year	2013	2014	2015	2016	2017	2018	2019
Code	A	B	C	D	E	F	G

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	100	V
Gate-Source Voltage	V_{GSS}	± 16	V
Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$	(Note 6) $T_A = +25^\circ\text{C}$	1.6	A
	$T_A = +70^\circ\text{C}$	1.3	A
	(Note 5) $T_A = +25^\circ\text{C}$	1.4	A
	$T_A = +70^\circ\text{C}$	1.1	A
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	0.6	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	8	A

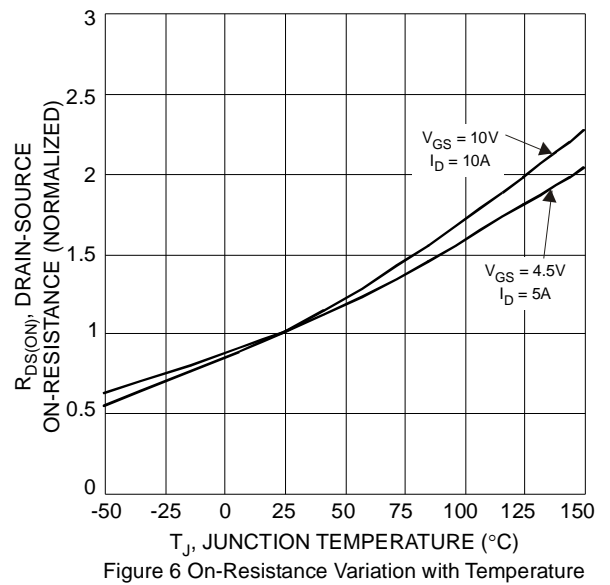
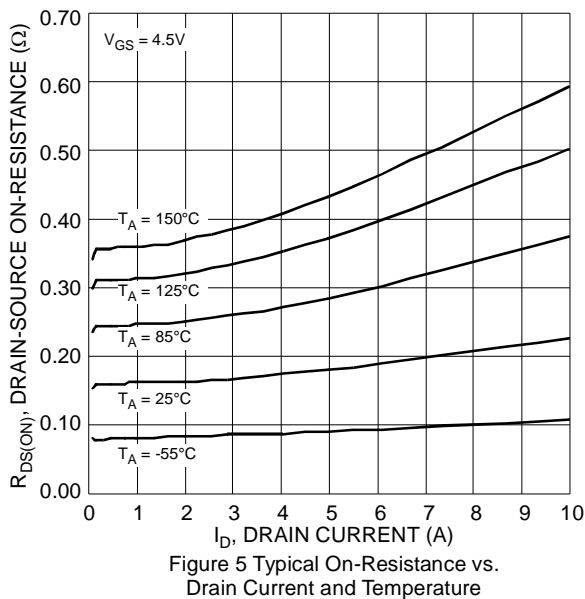
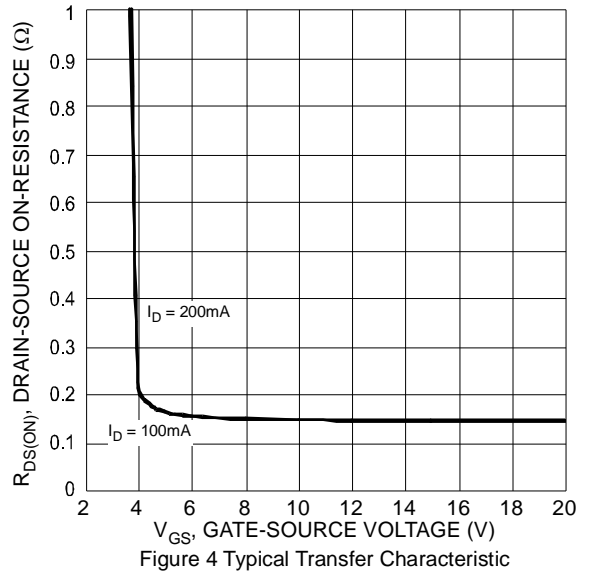
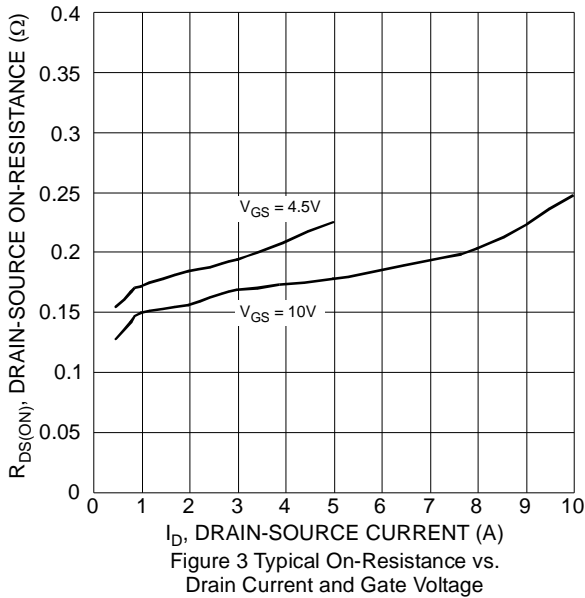
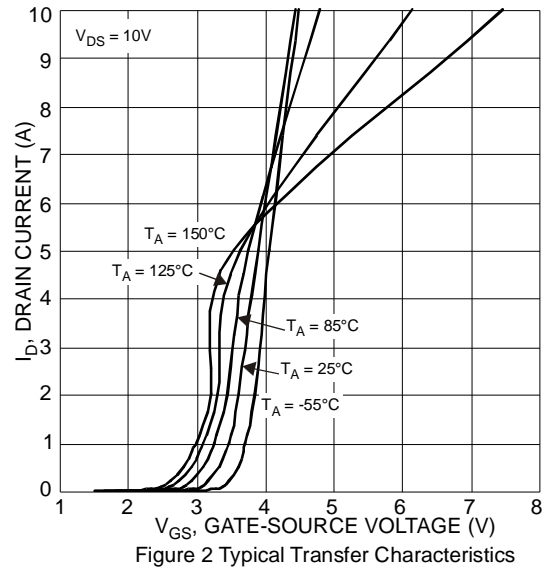
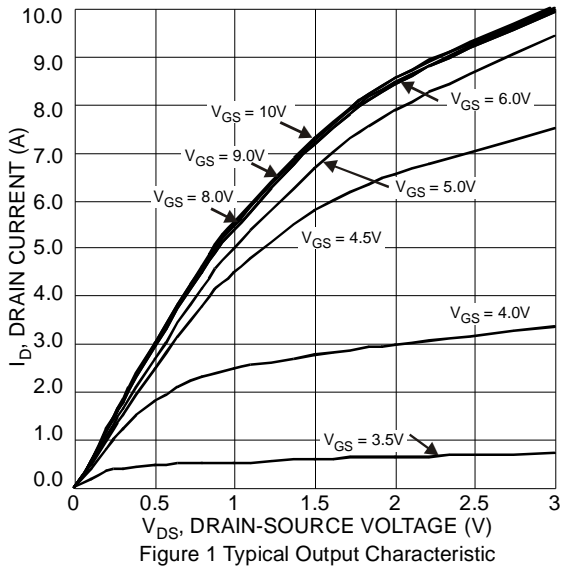
Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	P_D	$T_A = +25^\circ\text{C}$	1.3
		$T_A = +70^\circ\text{C}$	0.8
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	(Note 6)	94
		(Note 5)	177
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 100\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 16\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	220	m Ω	$V_{GS} = 10\text{V}, I_D = 1.6\text{A}$
			—	250		$V_{GS} = 4.5\text{V}, I_D = 1.3\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	$V_{GS} = 0\text{V}, I_S = 1.1\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	401	—	pF	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	22	—		
Reverse Transfer Capacitance	C_{rss}	—	17	—		
Gate Resistance	R_g	—	2.1	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	4.1	—	nC	$V_{DS} = 50\text{V}, I_D = 1.6\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	8.3	—		
Gate-Source Charge	Q_{gs}	—	1.5	—		
Gate-Drain Charge	Q_{gd}	—	2	—		
Turn-On Delay Time	$t_{D(on)}$	—	6.8	—	ns	$V_{DS} = 50\text{V}, V_{GS} = 4.5\text{V},$ $R_G = 6.8\Omega, I_D = 1\text{A}$
Turn-On Rise Time	t_r	—	8.2	—		
Turn-Off Delay Time	$t_{D(off)}$	—	7.9	—		
Turn-Off Fall Time	t_f	—	3.6	—		
Reverse Recovery Time	t_{rr}	—	17	—	ns	$I_F = 1.1\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{rr}	—	9.8	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.



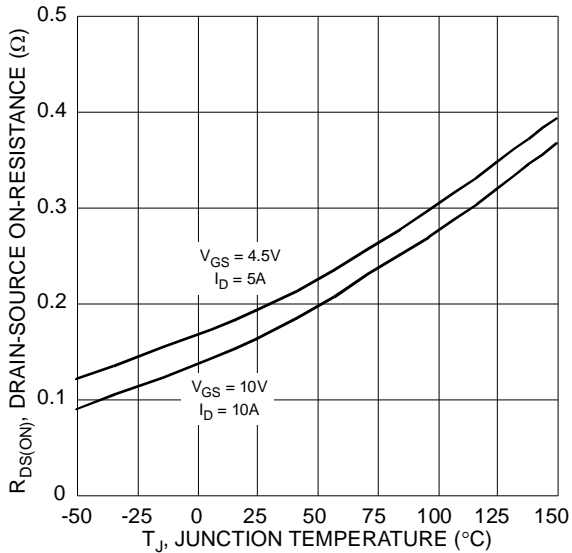


Figure 7 On-Resistance Variation with Temperature

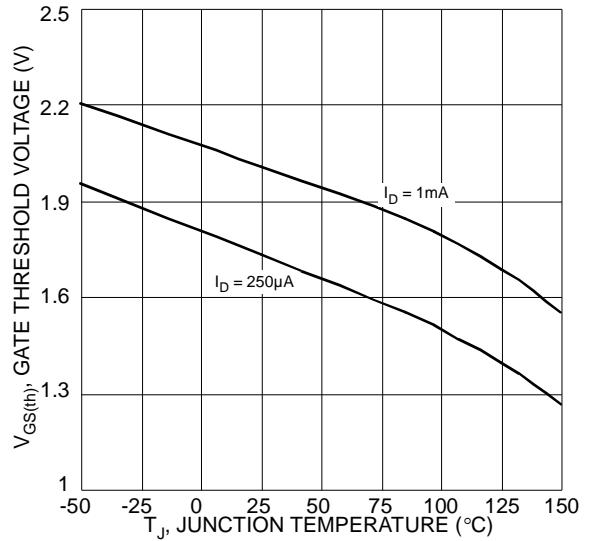


Figure 8 Gate Threshold Variation vs. Ambient Temperature

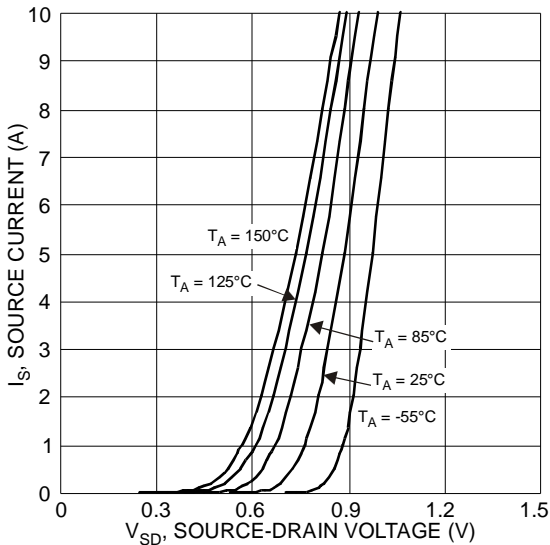


Figure 9 Diode Forward Voltage vs. Current

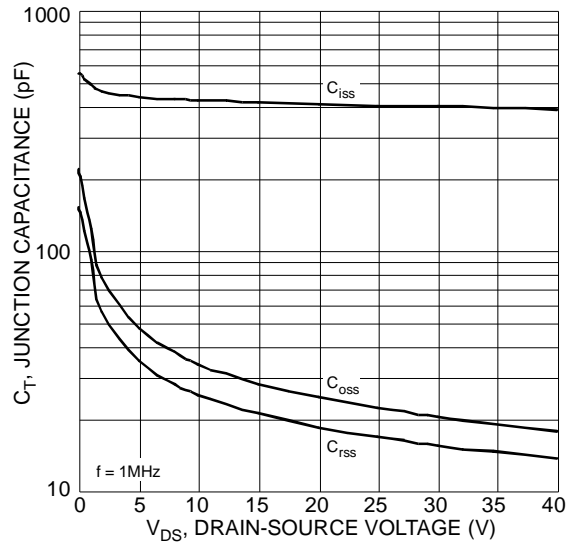


Figure 10 Typical Junction Capacitance

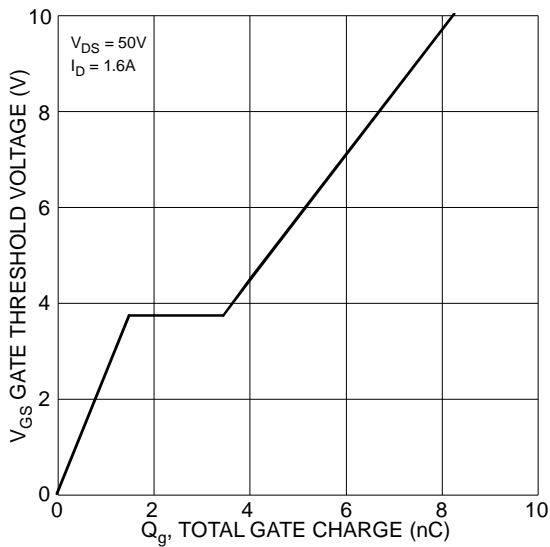


Figure 11 Gate Charge

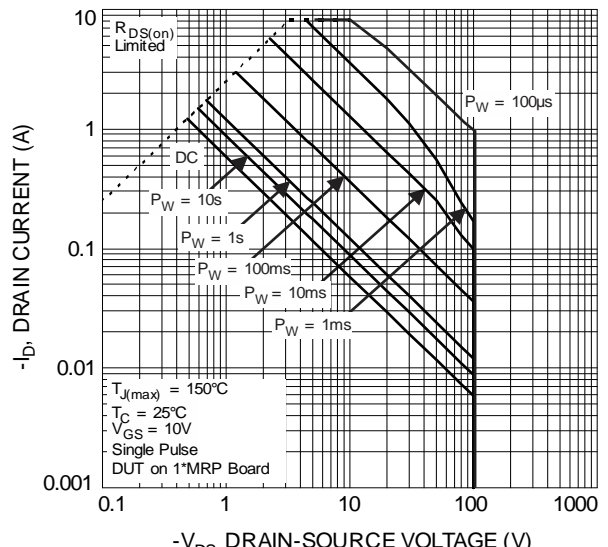
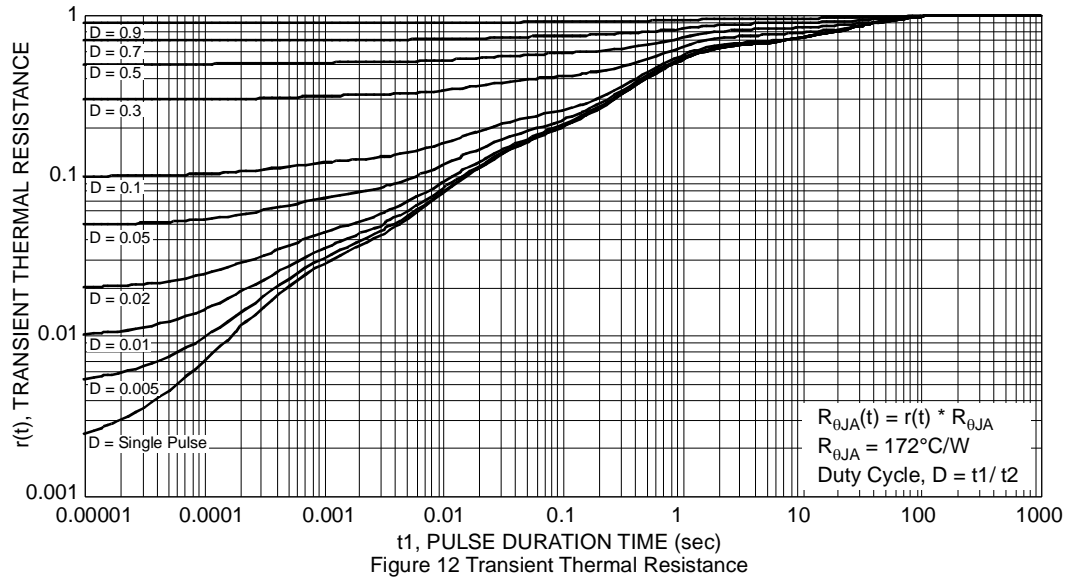
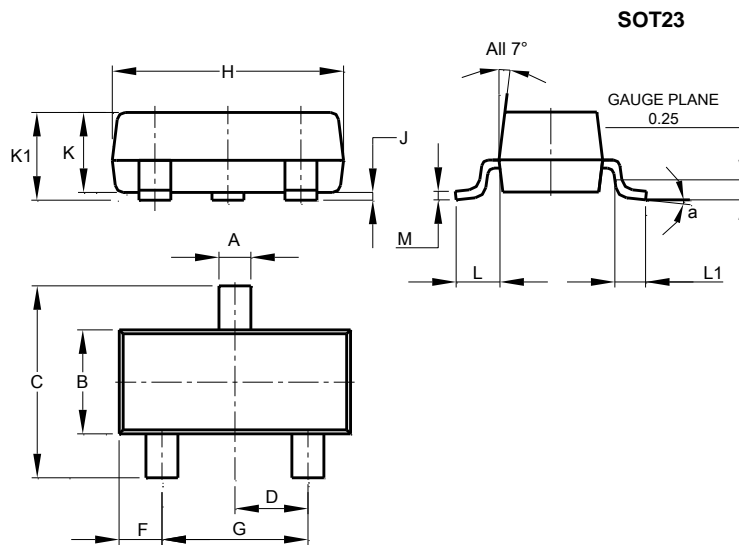


Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

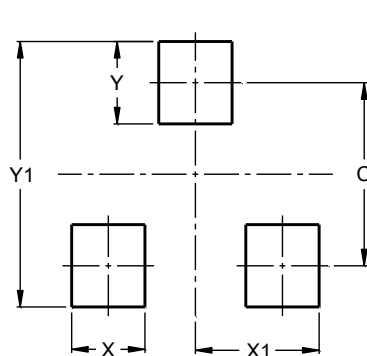
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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